

# Online Radiation Dose Measurement System for ATLAS experiment

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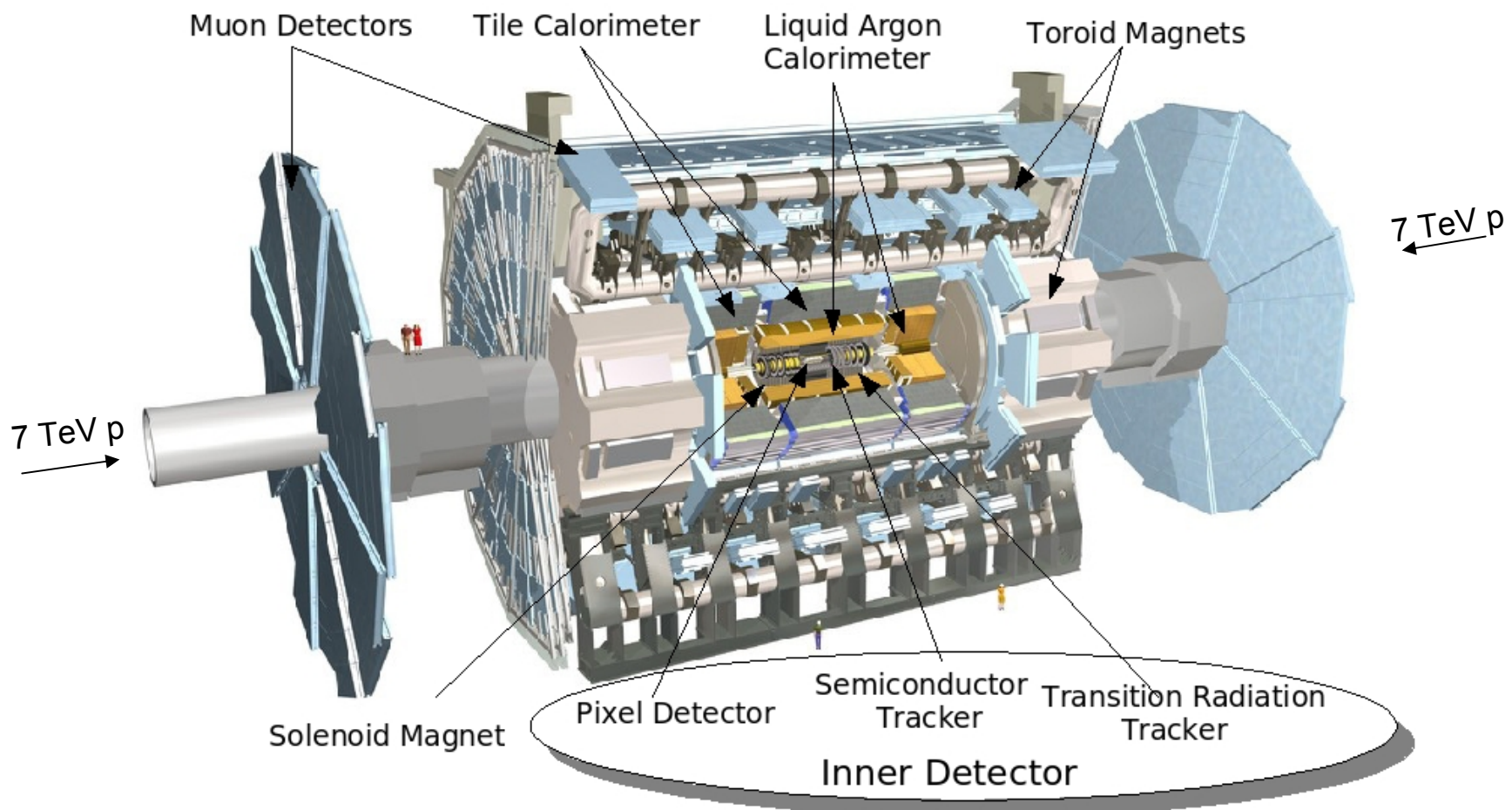
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# The ATLAS experiment

- experiment at the Large Hadron Collider at CERN
- proton-proton collisions,  $E_p = 7 \text{ TeV}$ , Luminosity =  $10^{34} \text{ cm}^{-2}\text{s}^{-1}$

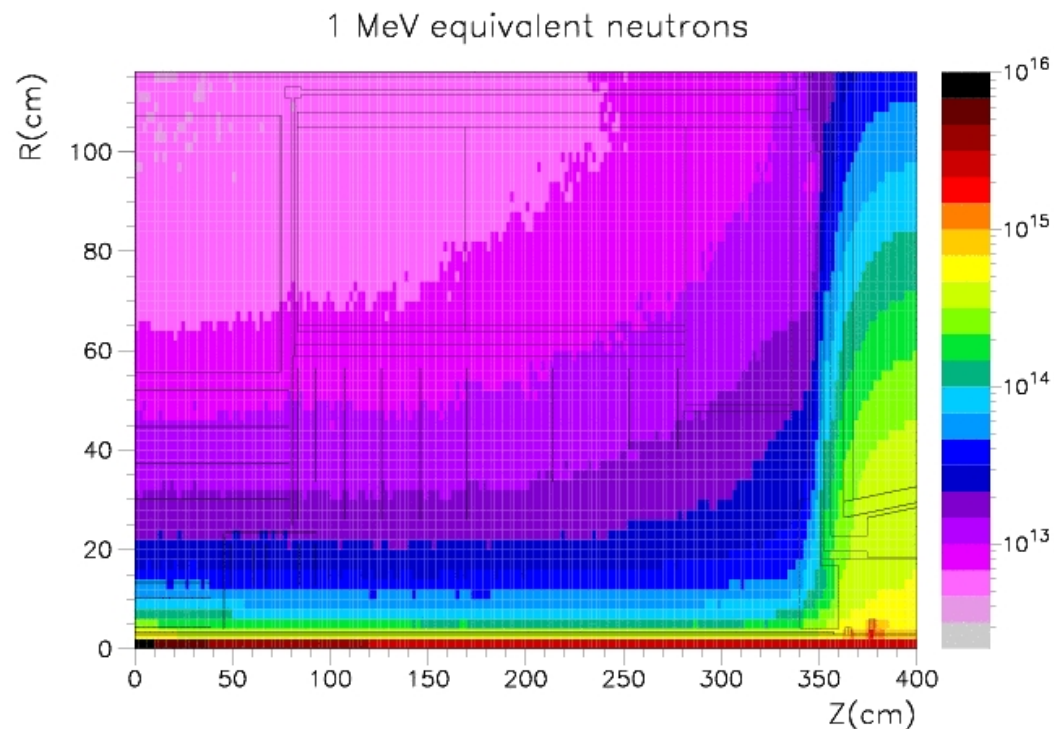


# Radiation Field in ATLAS

- secondary particles from p-p interaction point - mostly pions
- radiation from interaction of secondary particles with detector material - neutrons

Radiation levels after 10 years of LHC operation:

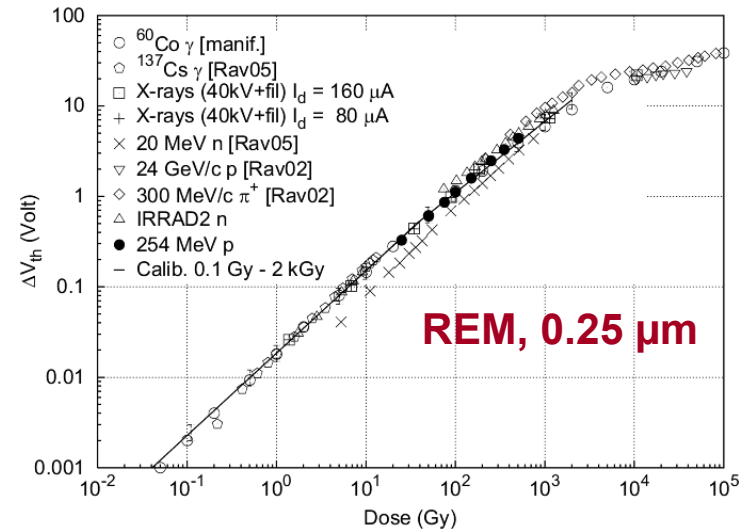
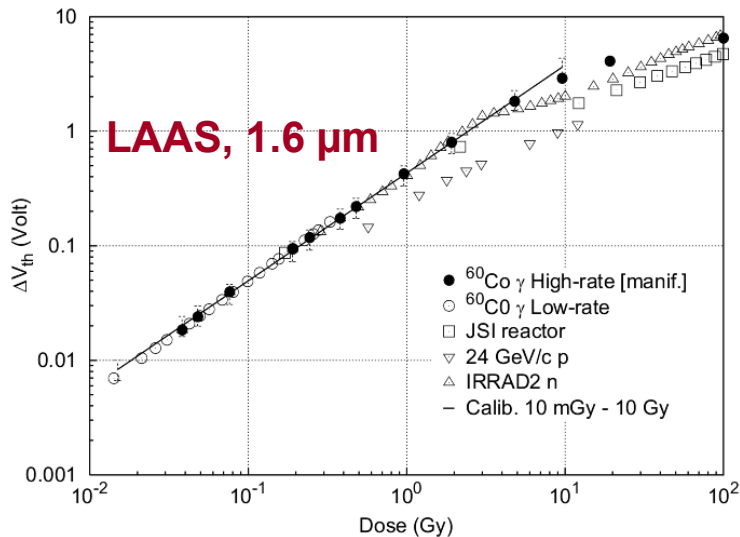
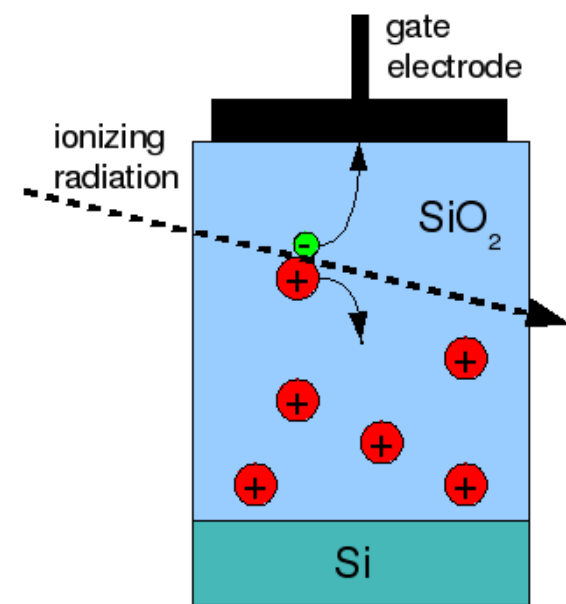
- Total Ionizing Dose (TID):  
TID > 100 kGy
- Non Ionizing Energy Loss (NIEL):  
 $\Phi_{eq} > 10^{15}$  n/cm<sup>2</sup>  
(1 MeV equivalent neutrons in Si)
- Thermal neutrons  $\Phi \sim 10^{15}$  n/cm<sup>2</sup>



- such radiation levels cause damage to detectors and readout electronics
  - ➔ dose monitoring necessary to understand detector performance
  - ➔ cross check of simulations and make predictions

# TID measurements with RadFETs

- RadFETs: p-MOS transistor
- holes created by radiation get trapped in the gate oxide:
  - ➔ increase of threshold voltage with dose:
 
$$\Delta V = a \times (TID)^b$$
- sensitivity and dynamic range depend on oxide thickness:



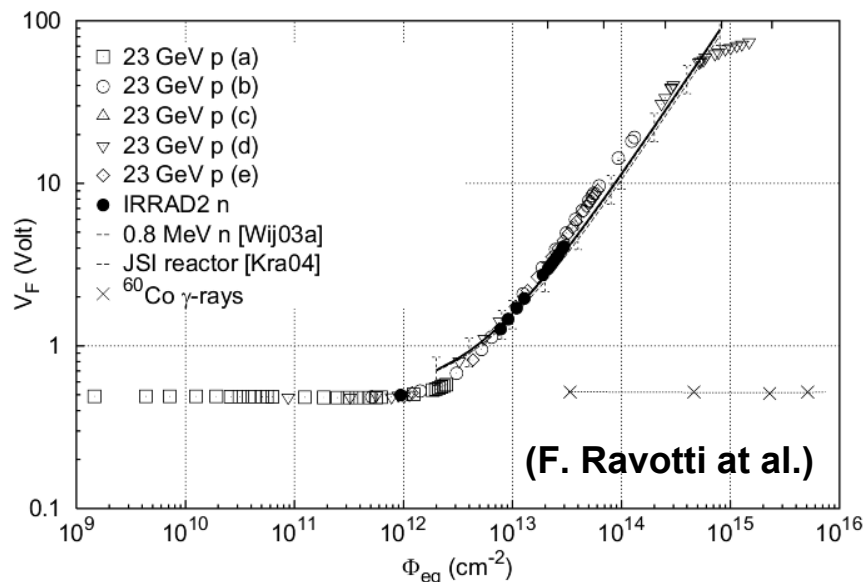
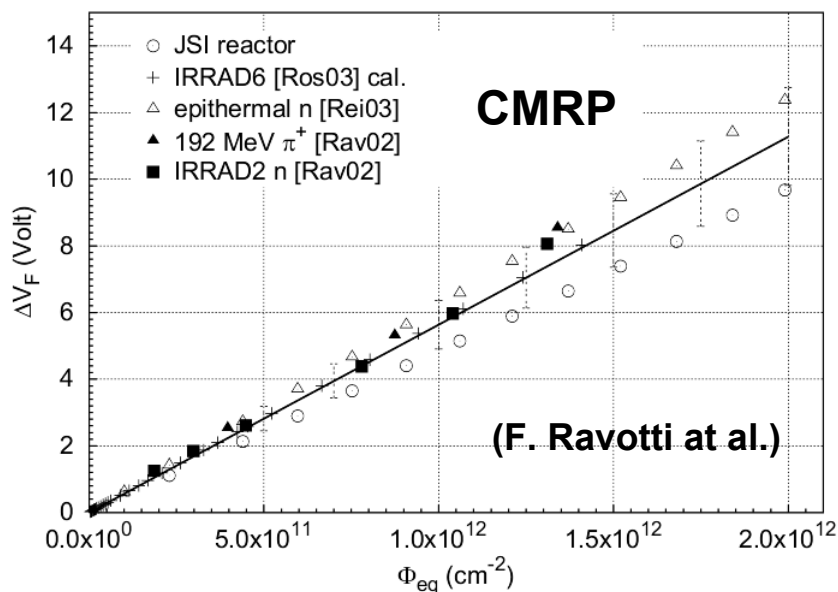
- characterizations, selection, calibrations done by CERN RADMON team:  
F. Ravotti, M. Glaser, M. Moll....

# NIEL measurements with diodes

- hadrons cause bulk damage in silicon. Consequences:
  - increased resistance, increase of reverse current.....
- ➔ forward bias: forward voltage at given forward current increases
- ➔ reverse bias: increase reverse current

## Forward bias

- linear response  $\Delta V = k \cdot \Phi_{eq}$  ( $V$  measured at  $I = 1 \text{ mA}$ )
- high sensitivity diode (CMRP, University of Wollongong, AU)  $10^9$  to  $\sim 10^{12} \text{ n/cm}^2$ ,
- commercial silicon PIN photodiode BPW34F  $10^{12}$  to  $\sim 10^{15} \text{ n/cm}^2$

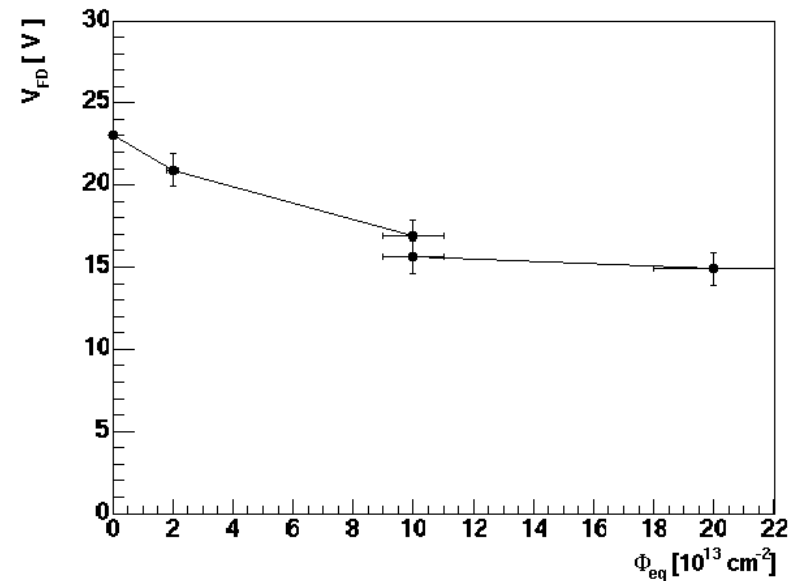
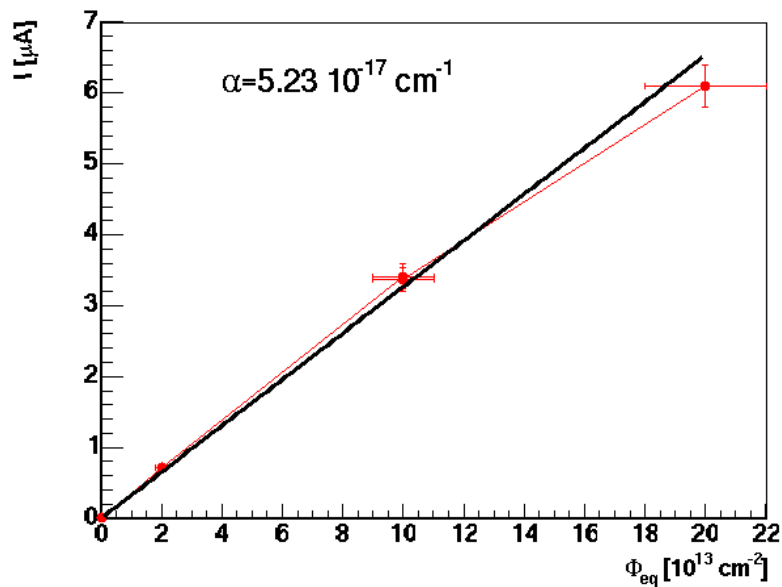


➔ sensitivity can be shifted to lower  $\Phi$  if diode is pre-irradiated with  $\sim 3 \cdot 10^{12} \text{ n/cm}^2$

## Reverse bias

Reverse current proportional to fluence  $I = \Phi_{eq}/\alpha V$

- **25  $\mu\text{m}$  x 0.5 cm x 0.5 cm** pad diode with guard ring structure processed on **epitaxial silicon**
  - **thin epitaxial** diode can be depleted with  $V_{\text{bias}} < 30$  V also after irradiation with  $10^{15}$  n/cm<sup>2</sup>
  - in this fluence and time range  $V_{\text{bias}}$  does not increase with annealing
- suitable for fluences from  $10^{11}$  n/cm<sup>2</sup> to  $10^{15}$  n/cm<sup>2</sup>



# Thermal neutrons

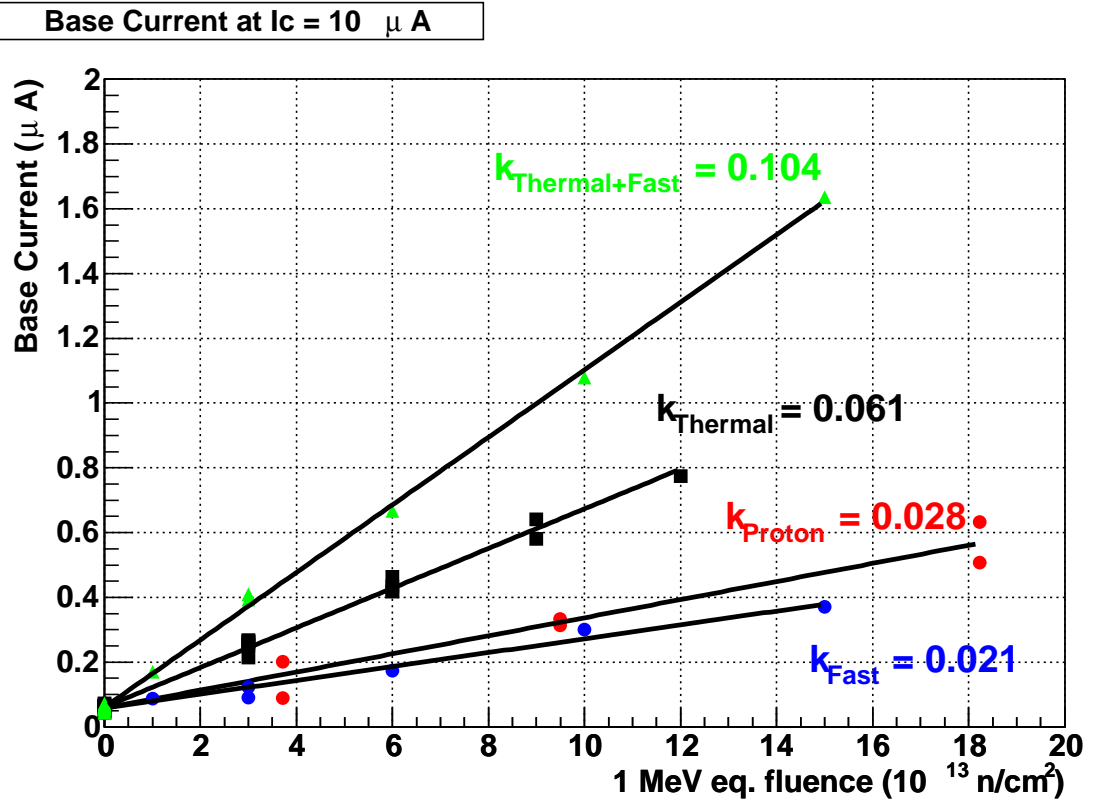
- bipolar transistors (DMILL) used in front end ASICs
- measure base current at given collector current

→ sensitive to fast and thermal neutrons

$$\Delta I_b / I_c = k_{eq} \cdot \Phi_{eq} + k_{th} \cdot \Phi_{th}$$

$k_{eq}$ ,  $k_{th}$  and  $\Phi_{eq}$  known

→  $\Phi_{th}$  can be determined  
(range:  $\sim 10^{12}$  to  $\sim 10^{15}$  n/cm<sup>2</sup>)



# Radiation Monitor Sensor Board (RMSB)

## Inner Detector

- for dose monitoring in the Inner Detector:

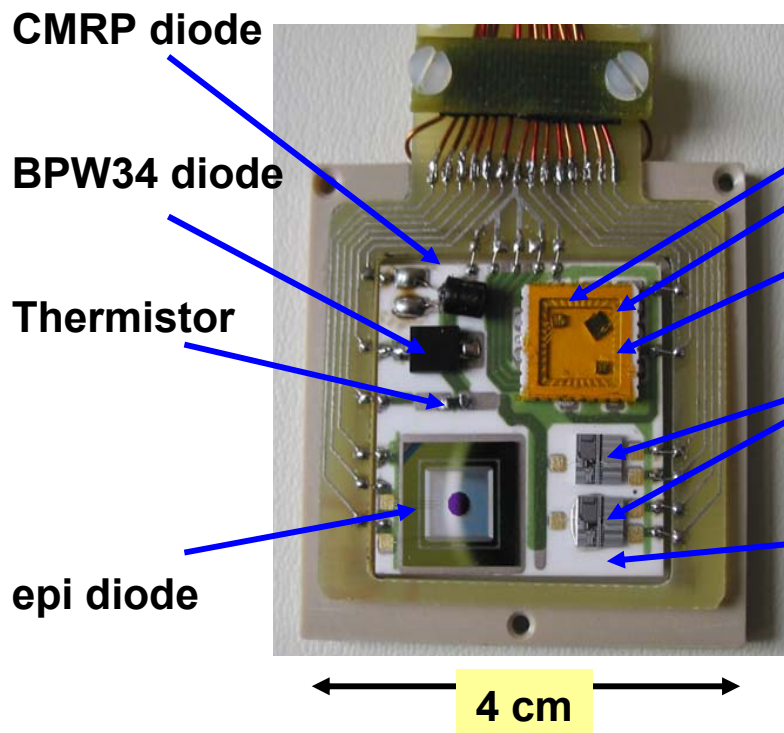
- large range of doses
- no access in 10 years

→ **need many sensors**

- large temperature variations (-10 to 20°C) at some locations

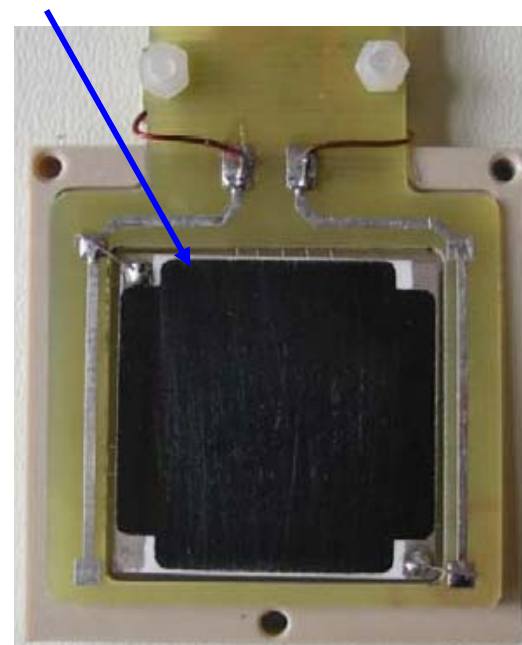
→ stabilize temperature to  $20 \pm 1$  °C by heating back side of the ceramic hybrid

**Thick film resistive layer  $R = 320 \Omega$**



Radfet package:

- $0.25 \mu\text{m SiO}_2$
- $1.6 \mu\text{m SiO}_2$
- $0.13 \mu\text{m SiO}_2$



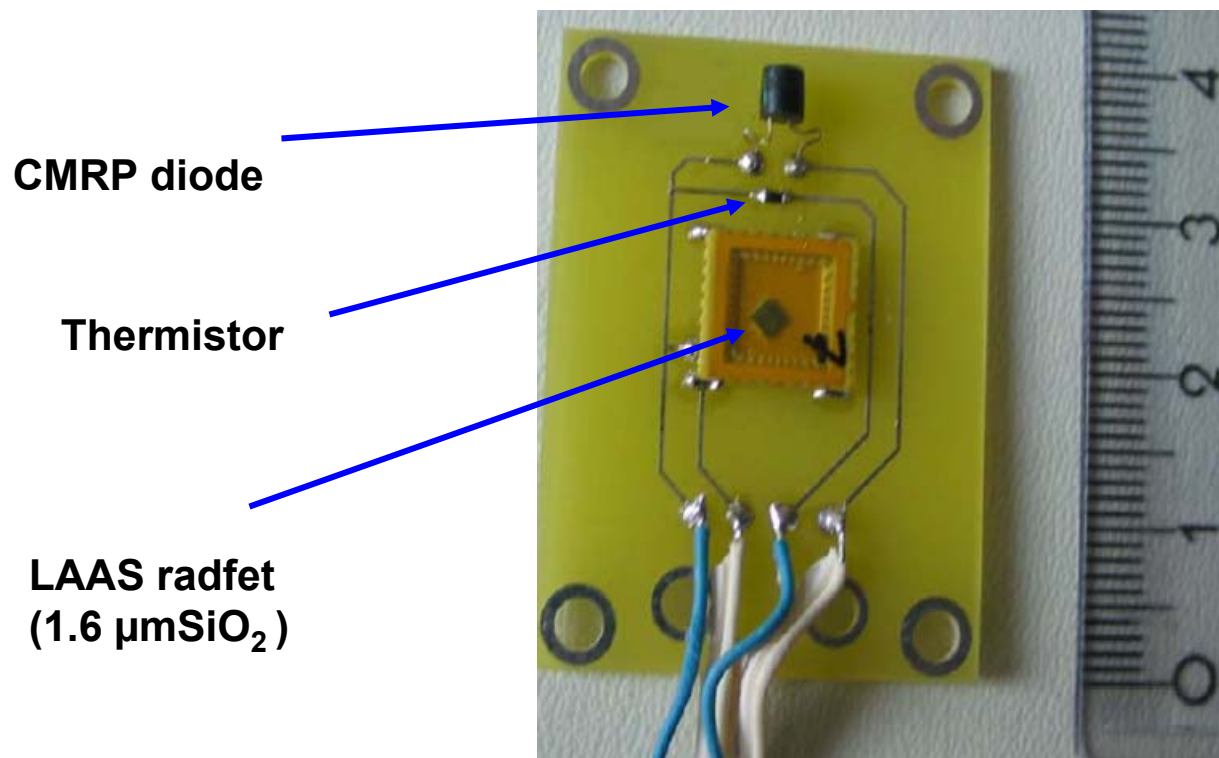
**Back side**



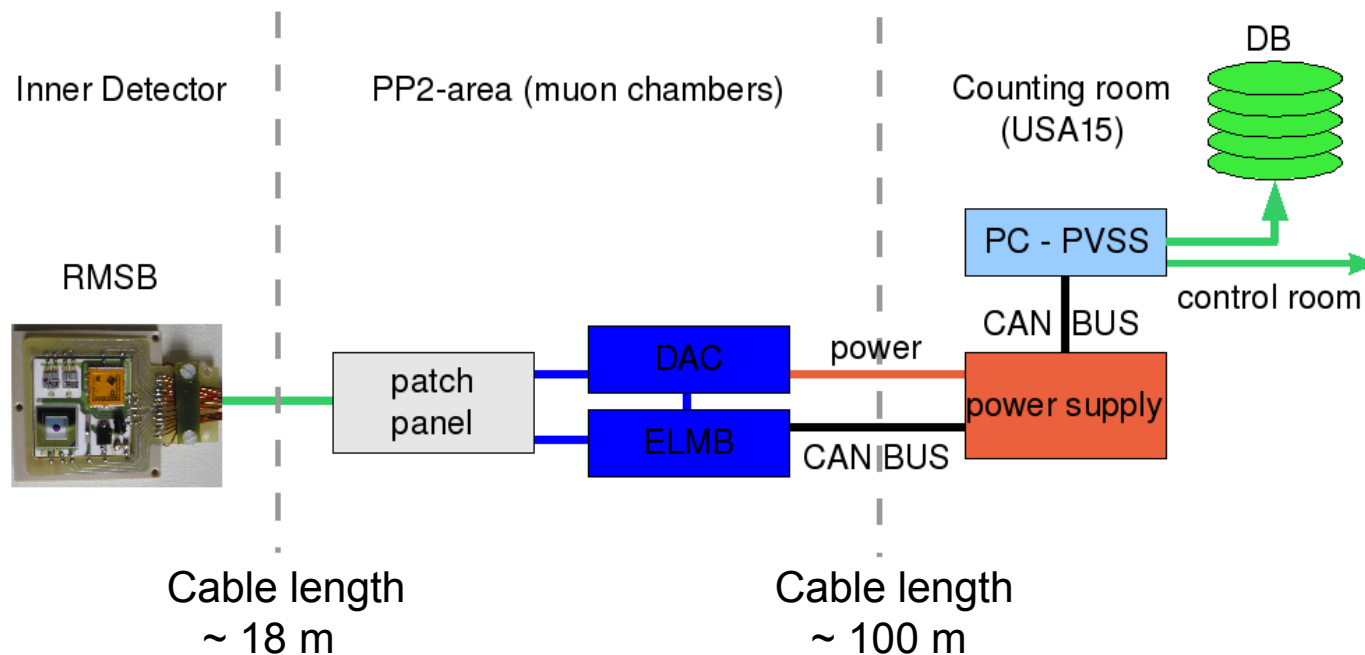
# Radiation Monitor Sensor Board (RMSB)

## Other locations

- lower dose ranges  
→ mGy to 10 Gy,  $10^9$  to  $\sim 10^{12}$  n/cm<sup>2</sup>
- no temperature stabilization  
→ correct read out values with known temperature dependences



- use standard ATLAS Detector Control System components
  - **ELMB:**
    - 64 ADC channels
    - can bus communication
  - **ELMB-DAC:**
    - current source, 16 channels ( $I_{\max} = 20 \text{ mA}$ ,  $U_{\max} = 30 \text{ V}$ )
- sensors are biased only during readout ( $\sim$  few minutes every hour)
- software written in PVSS
- readout values available in the ATLAS control room and archived for offline analysis



# Monitoring locations

- 14 monitors in the Inner Detector

Module Panel Scale Help

en\_US.iso88591

root 14-10-2008 15:16:41

**RADMON**

Sensors	READY	OK	
RMSB 1 (IDEP)	OPERATIONAL	OK	✓
RMSB 2 (IDEP)	OPERATIONAL	OK	✓
RMSB 3 (IDEP)	OPERATIONAL	OK	✓
RMSB 4 (IDEP)	OPERATIONAL	OK	✓
RMSB 5 (Cryo)	OPERATIONAL	OK	✓
RMSB 6 (PST)	OPERATIONAL	OK	✓
RMSB 7 (IDEP)	OPERATIONAL	OK	✓
RMSB 8 (IDEP)	OPERATIONAL	OK	✓
RMSB 9 (PST)	OPERATIONAL	OK	✓
RMSB 10 (Cryo)	OPERATIONAL	OK	✓
RMSB 11 (IDEP)	OPERATIONAL	OK	✓
RMSB 12 (IDEP)	OPERATIONAL	OK	✓
RMSB 13 (PST)	OPERATIONAL	OK	✓
RMSB 14 (PST)	OPERATIONAL	OK	✓

3D View All connected

RMSB 3 (IDEP)

**Sensor Information**

Alias  
IDE/RADMON/IDEP/Zp345/R80/Phi195 z=+345cm, r=80cm, phi=195°

T 20.13 °C	RadFET 1 2.45e-9 Gy	DMILL 1 ~2.19e+9 n/cm2
PIN 1 6.36e+9 n/cm2	RadFET 2 0.00e+0 Gy	DMILL 2 ~5.22e+10 n/cm2
PIN 2 ~7.46e+9 n/cm2	RadFET 3 1.08e-1 Gy	EPI 2.00e+7 n/cm2

NB: - RF values: Total Ionising Dose (TID)

**RADIATION MONITORING - Inner Detector**

Temperature (RMSB) graph showing fluctuations over time.

Monitor ID	TID (Gy)	TN (n/cm2)	EPI (n/cm2)	PIN (n/cm2)
IDE:CAN4/RMSB0	0.00	4e+010	1e+011	5e+010
IDE:CAN2/RMSB1	0.00	-1e+011	4e+007	1e+010
IDE:CAN2/RMSB0	0.00	-2e+009	2e+007	6e+009
IDE:CAN4/RMSB1	0.00	3e+009	1e+011	-8e+009
IDE:CAN5/RMSB0	0.00	-1e+011	2e+007	5e+009
IDE:CAN3/RMSB1	0.01	2e+011	4e+011	2e+010
IDE:CAN3/RMSB0	0.00	-1e+011	4e+007	6e+009
IDE:CAN7/RMSB0	0.00	-3e+009	2e+007	8e+009
IDE:CAN7/RMSB1	0.00	-5e+010	4e+007	8e+009
IDE:CAN8/RMSB0	0.00	1e+011	4e+007	1e+011
IDE:CAN8/RMSB1	0.00	-1e+011	4e+011	7e+010
IDE:CAN5/RMSB1	0.00	1e+011	4e+011	2e+010
IDE:CAN3/RMSB1	0.00	-1e+011	4e+007	6e+009
IDE:CAN3/RMSB0	0.00	-2e+009	2e+007	6e+009

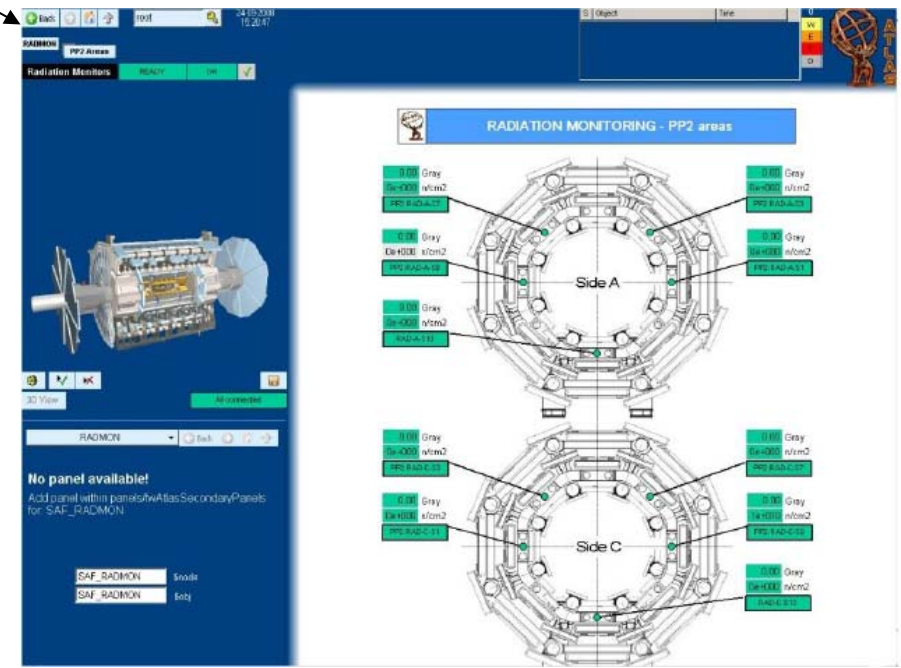
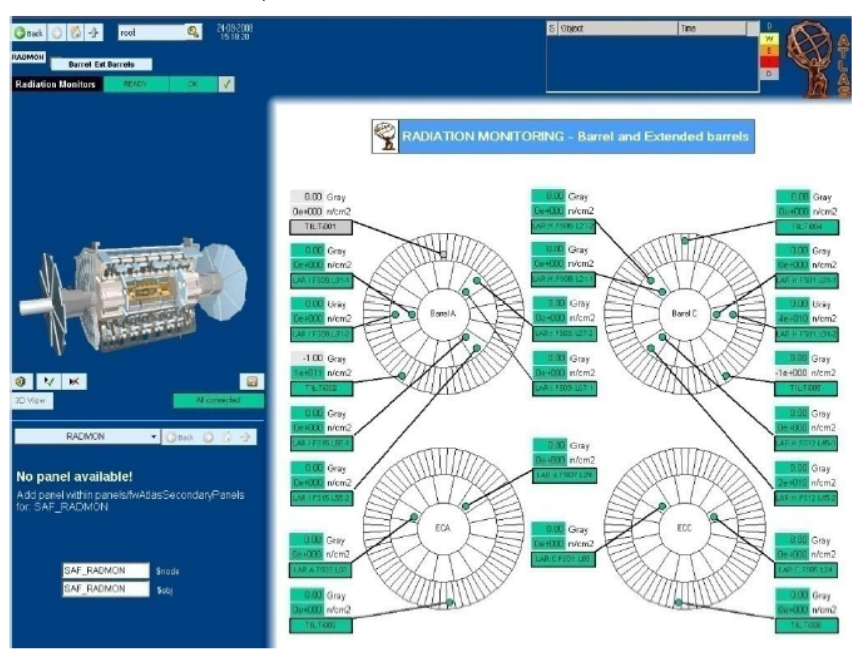
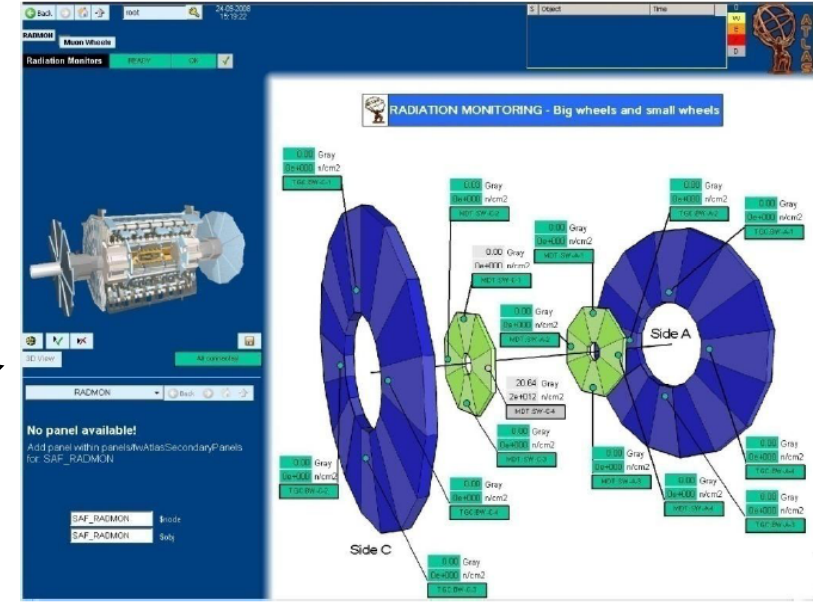
# Monitoring locations

- 48 locations outside if the Inner Detector

Muon detectors

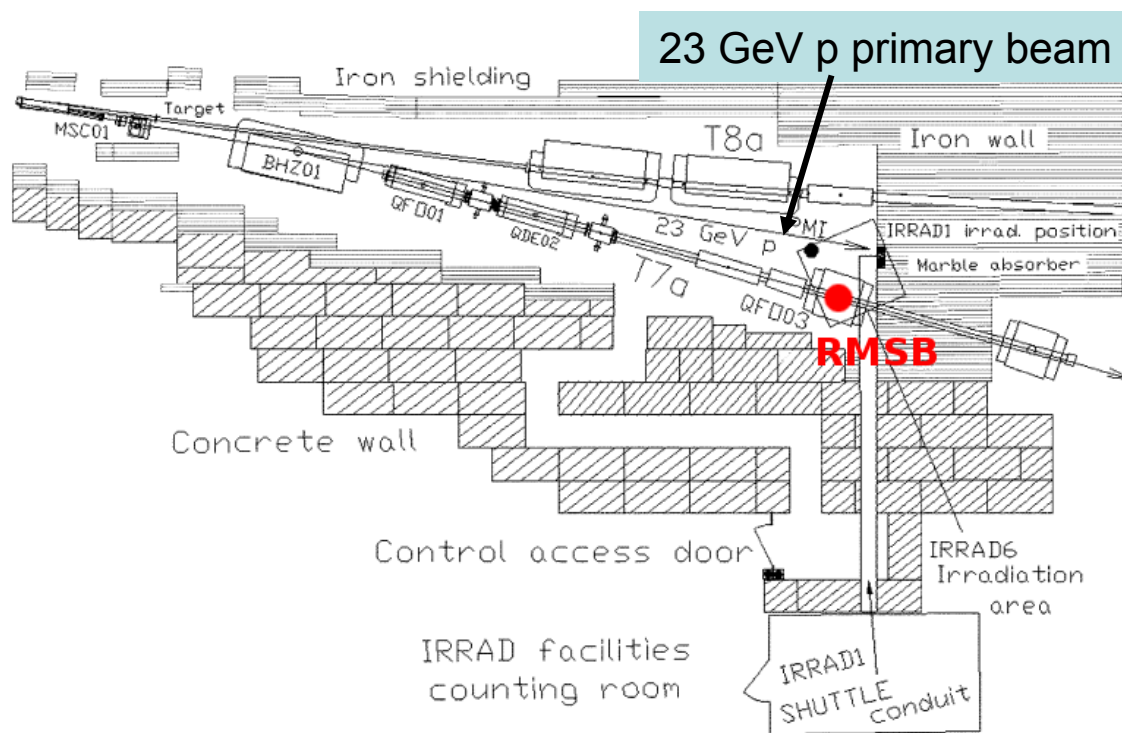
Calorimeters

TRT electronics



# Tests in Mixed Radiation Environment

- system with 2 ID-type RMSBs installed in the IRRAD6 irradiation facility at CERN in 2008
- mixture of pions, protons, neutrons, photons
- low dose rates, beam on-off
  - ➔ similar conditions as in ATLAS
- SEC counter Secondary Emission Counter (SEC): counts number of protons in primary beam
  - ➔ this number is proportional to the dose at RMSB location



F. Ravotti, M. Glaser et al., *IEEE TNS Vol. 54 (4), pp. 1170-1177, 2007.*

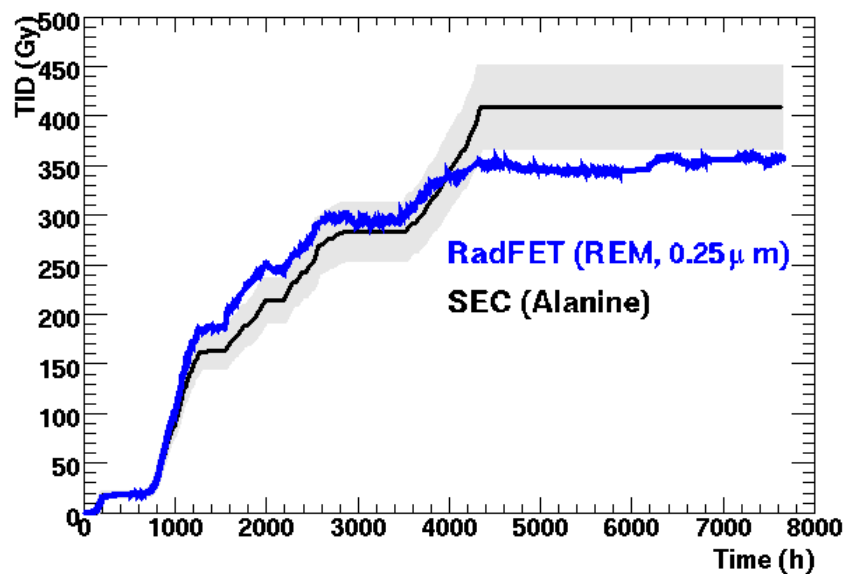
# Tests in Mixed Radiation Environment

## TID

- SEC counts converted to dose (Gy) with alanine dosimeter
  - dose  $410 \pm 20$  Gy measured with **alanine** at the end of beam period (at **4000 h**)

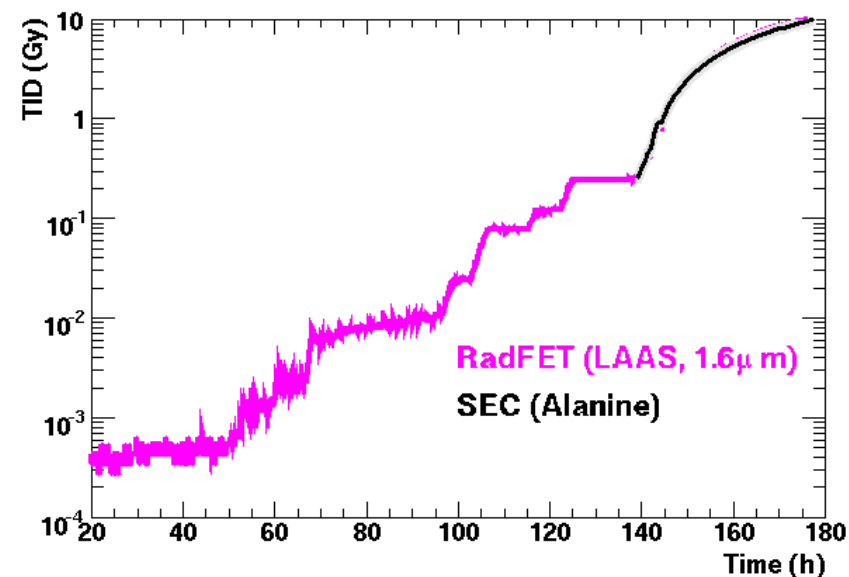
### Medium Sensitivity

- good agreement with SEC
- no significant annealing



### High Sensitivity RadFET

- mGy sensitivity



# Tests in Mixed Radiation Environment

## NIEL

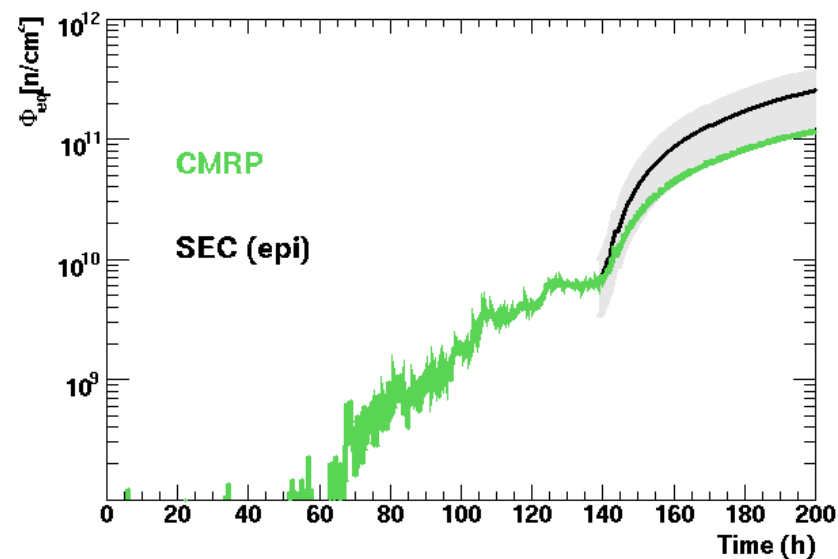
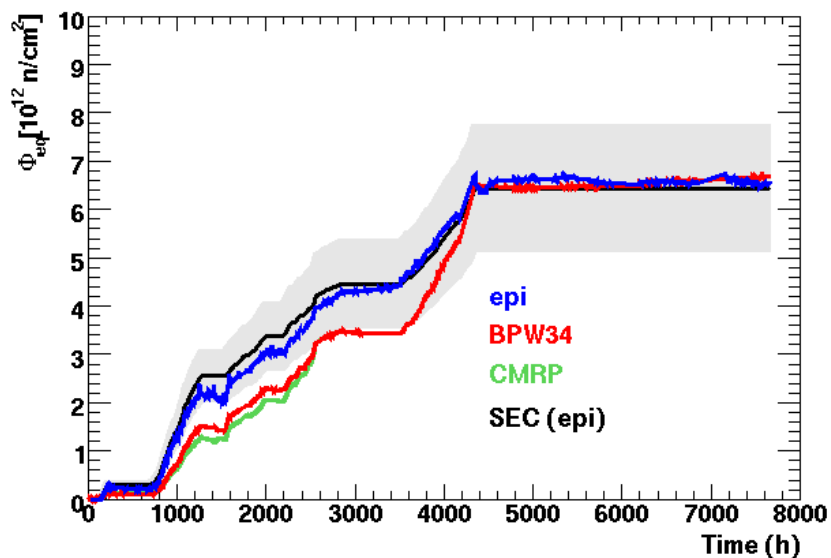
- SEC counts converted to 1 MeV equivalent neutron fluence with epitaxial diode on RMSB  
→ fluence  $\Phi_{eq} = 6.5 \cdot 10^{12} \text{ n/cm}^2$  at the end of beam period (at  $t = 4000 \text{ h}$ )

All diodes:

- epi -> reverse bias
- BPW34 -> forward bias
- CMRP -> forward bias  
→ epi and BPW34 corrected for annealing

High Sensitivity PiN diode (CMRP)

- measure forward bias @  $I = 1 \text{ mA}$   
→ sensitivity  $\sim 10^9 \text{ n/cm}^2$



# Tests in Mixed Radiation Environment

## Thermal neutrons

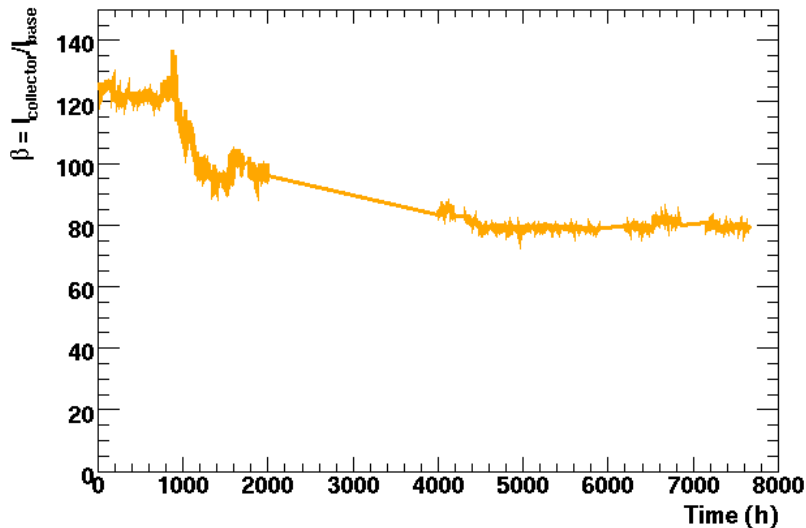
- base current  $I_b$  measured at collector current  $I_c = 10 \mu\text{A}$

1. monitor current gain  $\beta = I_c/I_b$

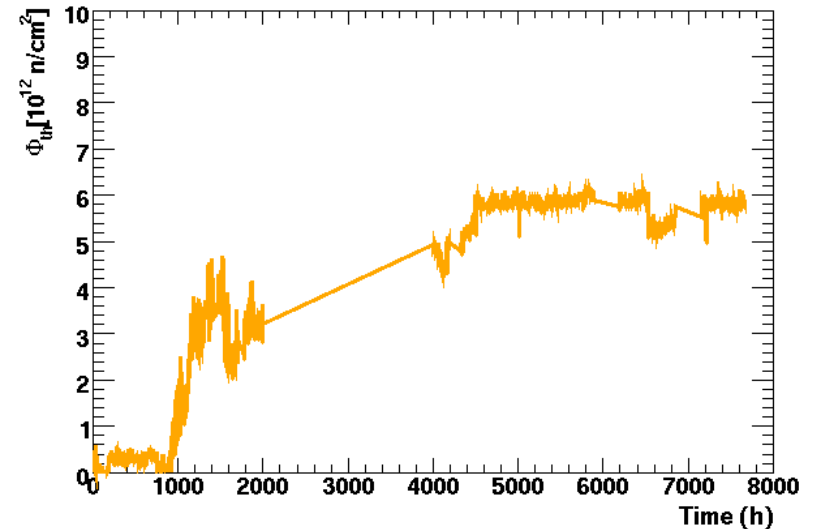
2. measure fluence of thermal neutrons:

$$\rightarrow \Phi_{th} = 1/k_{th} (\Delta I_b/I_c - k_{eq} \cdot \Phi_{eq}), \quad \Phi_{eq}: \text{measured with BPW34}$$

$\beta$  degradation



Thermal neutron fluence





- system for online radiation monitoring in ATLAS detector:
  - total ionizing dose in SiO<sub>2</sub>
  - bulk damage in silicon: 1 MeV equivalent neutron fluence
  - fluence of thermal neutrons (Inner Detector only)
  - readout compatible with ATLAS Detector Control System
- tests in mixed radiation environment
  - sufficient sensitivity: TID ~ mGy,  $\Phi_{eq} \sim 10^9 \text{ n/cm}^2$
  - sufficient accuracy: ~ 20%
  - annealing effect can be controlled

- complete system was installed and integrated in ATLAS DCS in 2008
  - few months of data taking in 2008
  - good stability

**Ready to measure doses!**

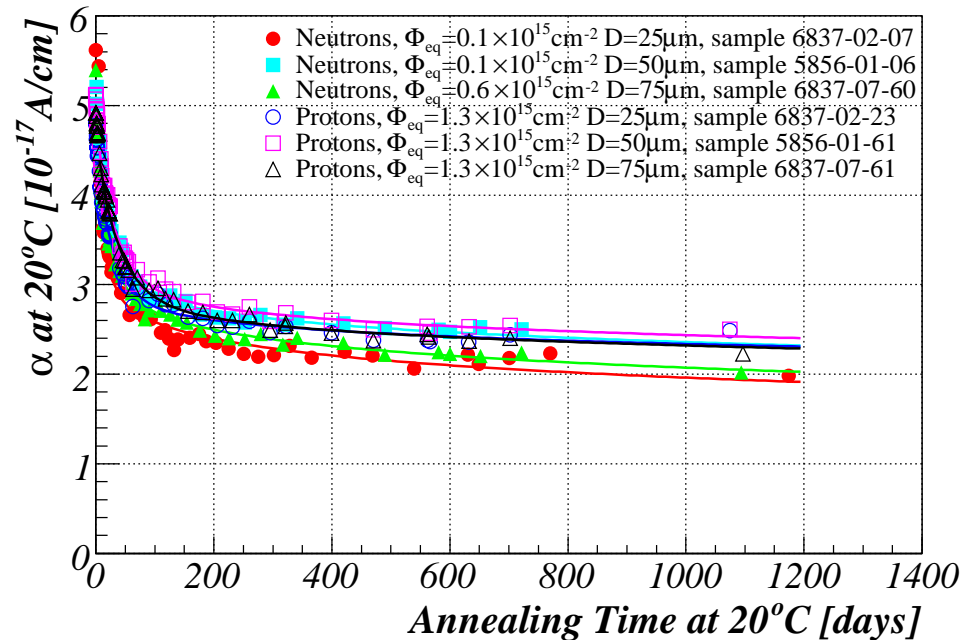
## Annealing:

- approximation:

$$I(t) = I_1(t) + I_0$$

$$I_1(t) = V\Phi\alpha_1 \cdot e^{-\frac{t}{\tau}}; \quad I_0 = V\Phi\alpha_0$$

$$dI(t) = -\frac{I_1(t)}{\tau} dt$$



- increase of current  $\Delta I$  measured at time  $t$  in IRRAD6 after time interval  $\Delta t$ :

$$\Delta I = \alpha V \Delta \Phi - \frac{dI(t)}{dt} \cdot \Delta t$$

$$\Delta I = \alpha V \Delta \Phi - \frac{I_1(t)}{\tau} \cdot \Delta t$$

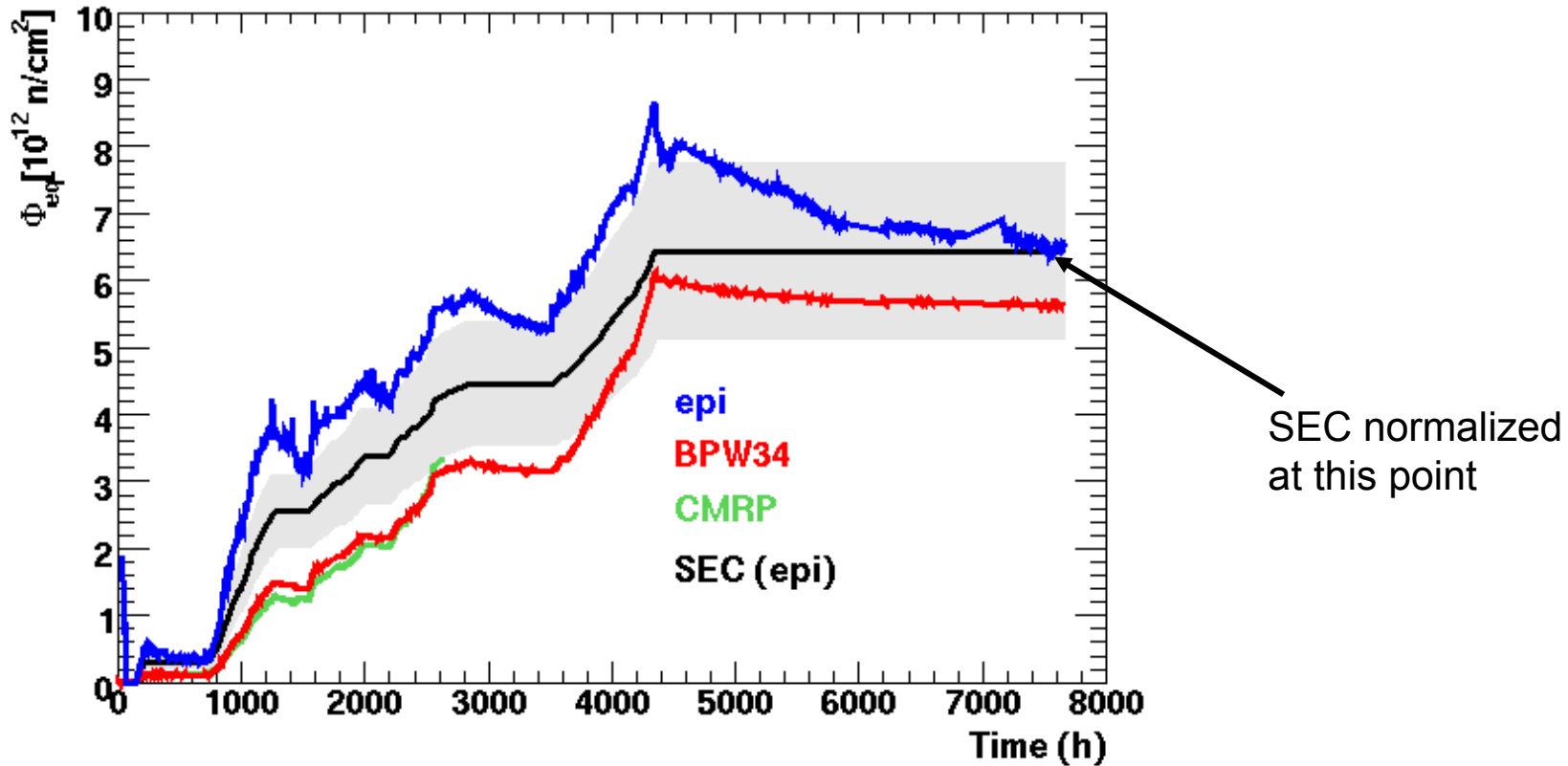
$$I_1(t) = I(t) - V\alpha_0\Phi(t)$$

$$\alpha = \alpha_1 + \alpha_0$$

$$\Delta \Phi = \frac{1}{\alpha V} \left( \Delta I + \frac{I_1(t)}{\tau} \cdot \Delta t \right)$$

# Appendix: Tests in Mixed Radiation Environment

Annealing:



• raw measurements (no corrections for annealing)